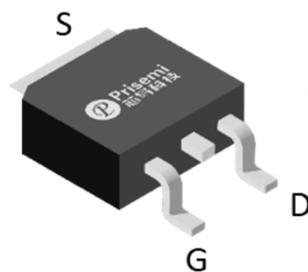


## Description

Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ)	I <sub>D</sub> (A)
700	320	6

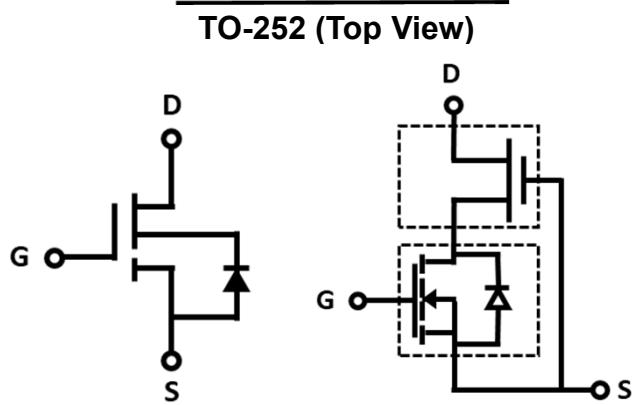


## Feature

- Easy to use, compatible with standard gate drivers
- Excellent Q<sub>G</sub> × R<sub>DS(on)</sub> figure of merit (FOM)
- Low Q<sub>RR</sub>, no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free

## Applications

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors



Schematic Symbol

Cascode  
Device Structure

## Absolute maximum rating@25°C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	700	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Transient Drain-Source Voltage <sup>1)</sup>	V <sub>TDS</sub>	800	V
Continuous Drain Current	I <sub>D</sub>	6	A
		3.7	
Pulsed Drain Current (Pulse Width: 100μs)	I <sub>DM</sub>	20	A
		13.5	
Power Dissipation	P <sub>D</sub>	20	W
Soldering Peak Temperature	T <sub>CSOLD</sub>	260	°C
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

## Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	-	6.2	-	°C/W
Thermal Resistance, Junction-to-Ambient <sup>2)</sup>	R <sub>θJA</sub>	-	50	-	°C/W

# 700V GaN Power Transistor

PGCDP70R320B

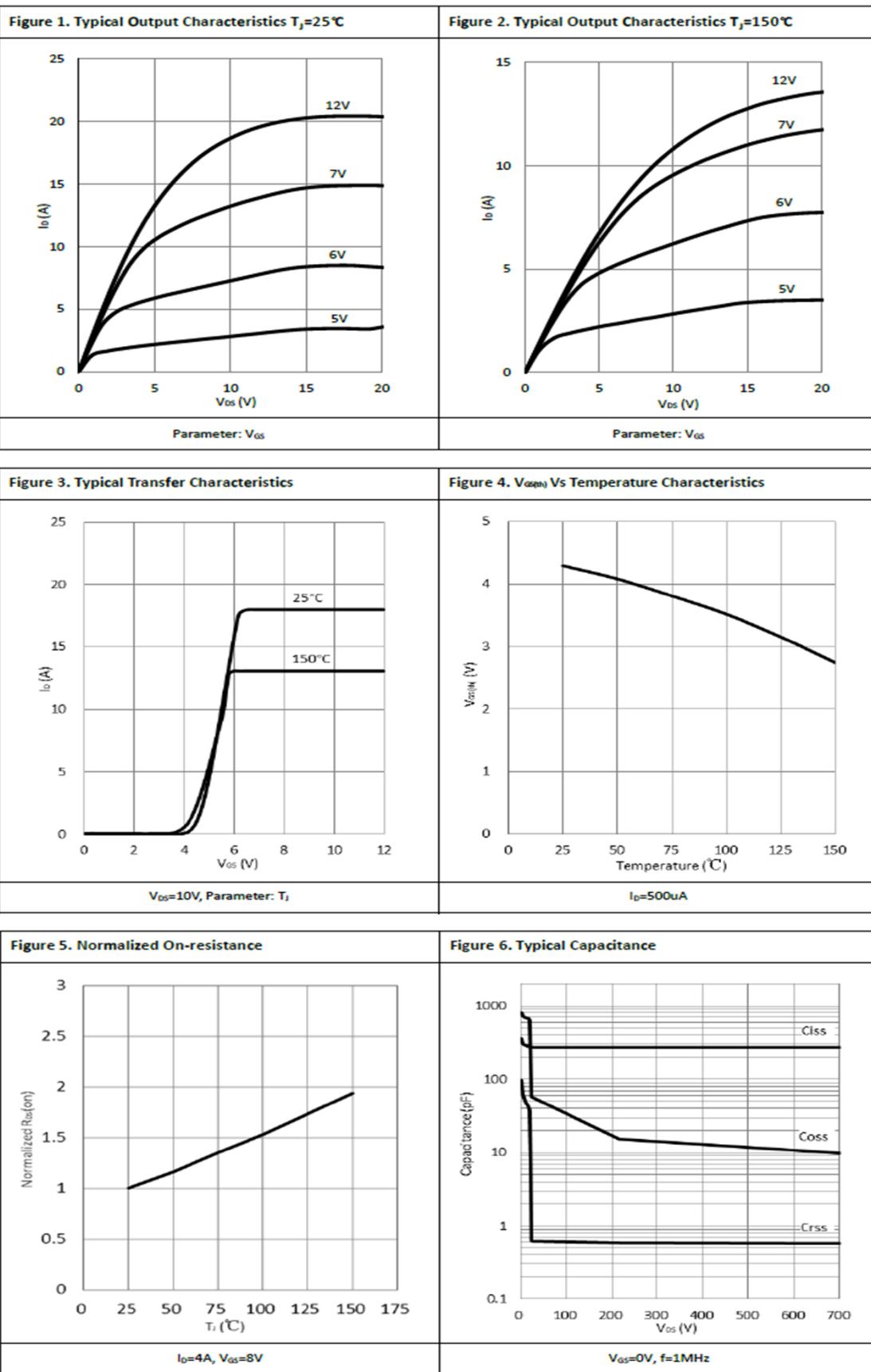
## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Units	
<b>Statistic Characteristics</b>								
Maximum Drain-Source Voltage	V <sub>DS-Max</sub>	V <sub>GS</sub> = 0V		700	-	-	V	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA		-	1000	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =700V, V <sub>GS</sub> =0V	T <sub>J</sub> =25°C	-	4	15	μA	
			T <sub>J</sub> =150°C	-	30	-		
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V		-	-	±150	nA	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 500μA	3	4	5	-	V	
Gate threshold voltage temperature coefficient	△V <sub>GS(th)</sub> /T <sub>J</sub>			-	-13	-	mV/°C	
Drain-Source On-State Resistance <sup>3)</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =8V, I <sub>D</sub> =4A	T <sub>J</sub> =25°C	-	320	400	mΩ	
			T <sub>J</sub> =150°C	-	640	-		
<b>Dynamic Characteristics</b>								
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V, f = 1MHz	- - -	274	-	-	pF	
Output Capacitance	C <sub>oss</sub>			12.6	-	-		
Reverse Transfer Capacitance	C <sub>rss</sub>			0.6	-	-		
Effective Output Capacitance, Energy Related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V	- - -	18.4	-	-	pF	
Effective Output Capacitance, Time Related	C <sub>o(tr)</sub>			55.4	-	-		
Output Charge	Q <sub>oss</sub>			22.1	-	nC		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 400V, I <sub>D</sub> = 4A, V <sub>GS</sub> = 0-12V, R <sub>G</sub> = 47Ω	- - - -	20	-	-	ns	
Turn-on Rise Time	t <sub>r</sub>			12	-	-		
Turn-Off Delay Time	t <sub>d(off)</sub>			72	-	-		
Turn-Off Fall Time	t <sub>f</sub>			12	-	-		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 400V, I <sub>D</sub> = 6A, V <sub>GS</sub> = 0-18V	- - -	6.5	-	-	nC	
Gate-Source Charge	Q <sub>gs</sub>			2	-	-		
Gate-Drain Charge	Q <sub>gd</sub>			2.3	-	-		
<b>Reverse Diode Characteristics</b>								
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A		-	1.5	-	V	
		V <sub>GS</sub> =0V, I <sub>S</sub> =6A	T <sub>J</sub> =25°C	-	2.2	-		
			T <sub>J</sub> =150°C	-	3.3	-		
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =6A, V <sub>DD</sub> =400V, di/dt=1000A/μs		-	14.2	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>			-	22.1	-	μC	

Notes:

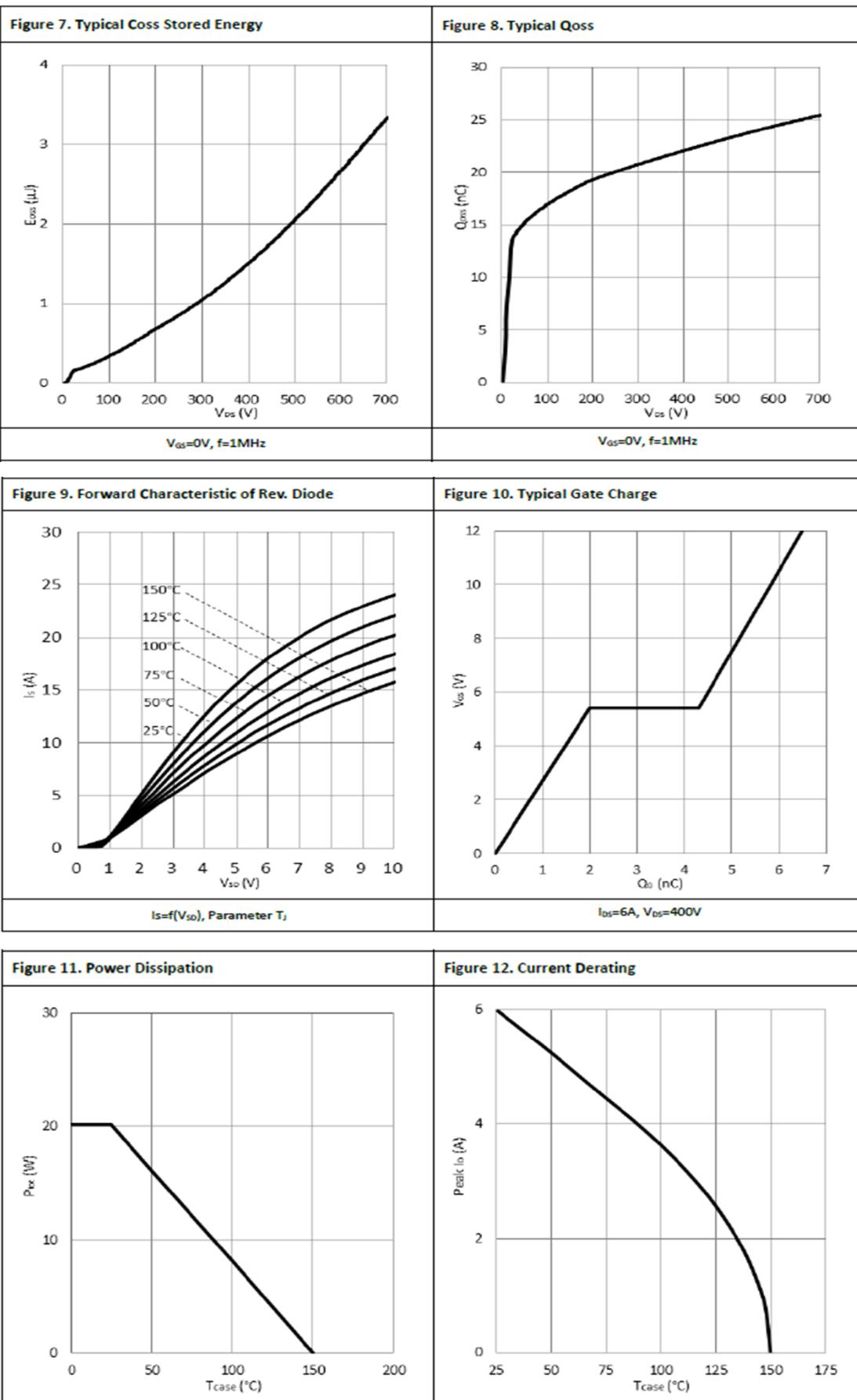
1. Off-state spike duty cycle < 0.01, spike duration < 2μs
2. Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm<sup>2</sup>copper area and 70μm thickness)
3. Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

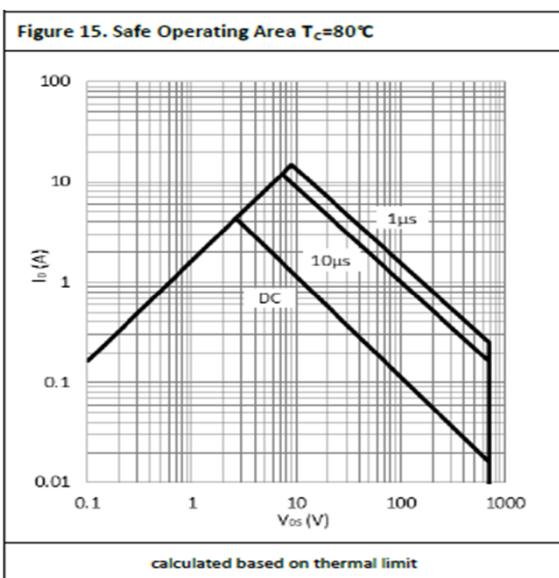
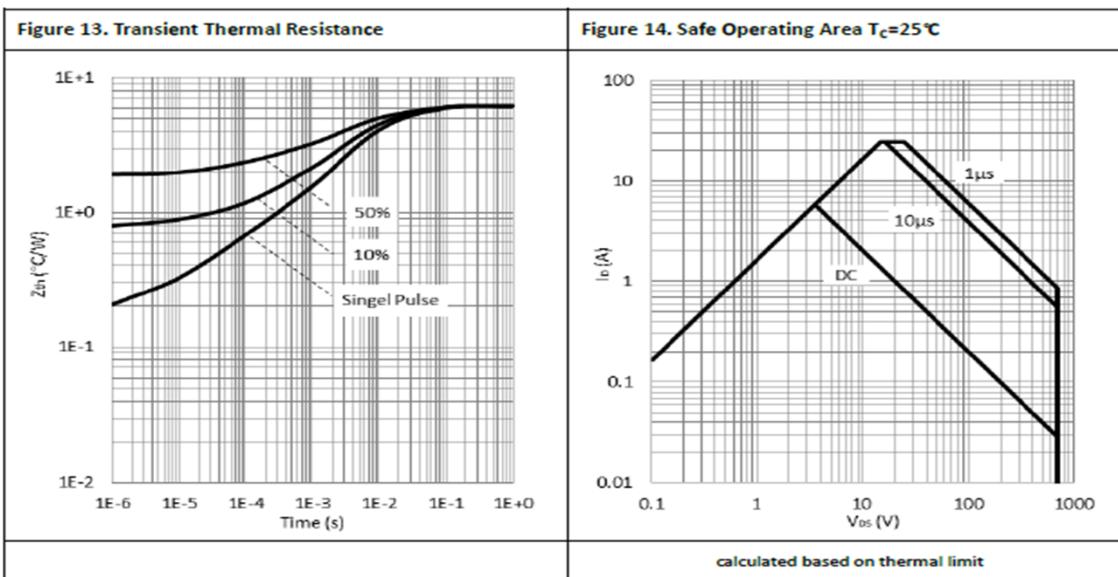
## Typical Characteristics



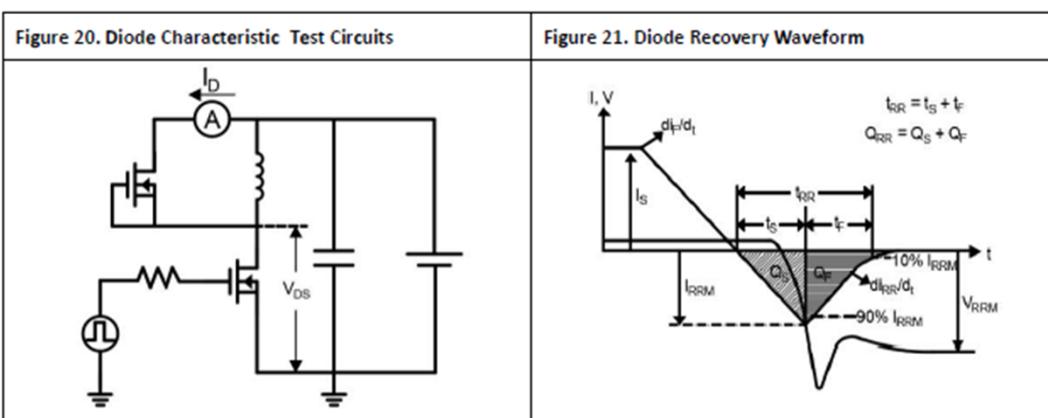
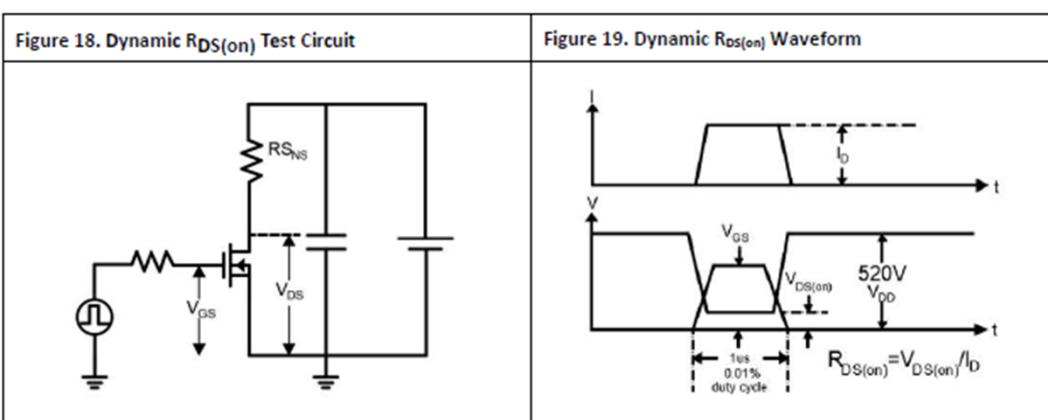
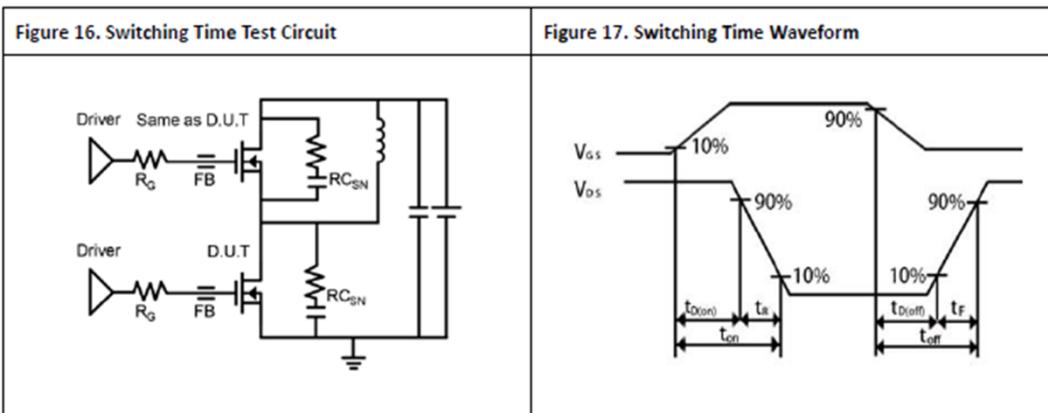
# 700V GaN Power Transistor

PGCDP70R320B

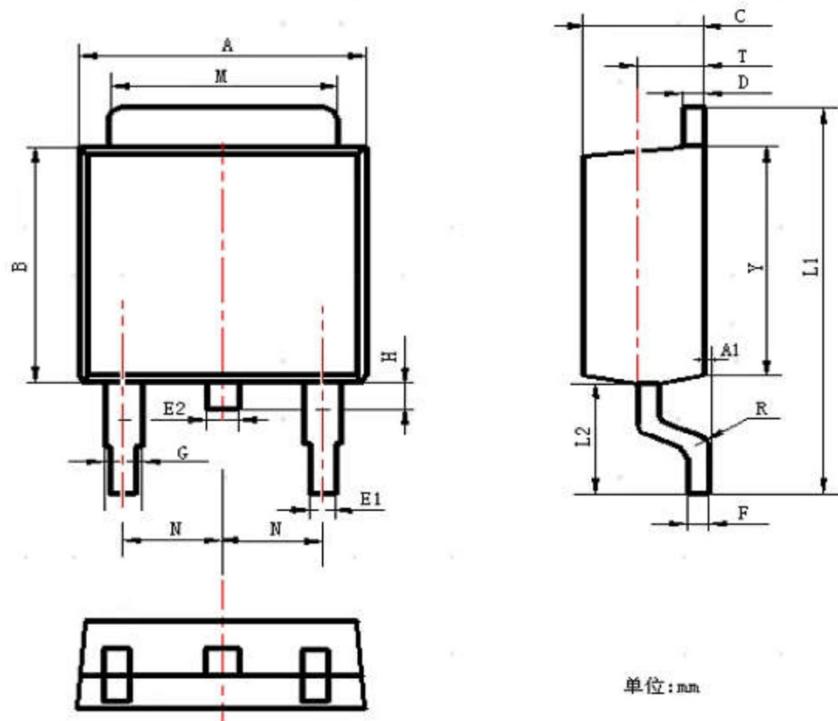




## Test Circuits and Waveforms



## Product Dimension (TO-252)



SYMBOL	Millimeter		
	Min	Nom	Max
A	6.30	6.60	6.90
A1	0	0.80	0.16
B	5.70	6.00	6.30
C	2.10	2.30	2.50
D	0.30	0.60	0.90
E1	0.60	0.75	0.90
F	0.30	0.45	0.60
G	0.70	0.95	1.20
L1	9.30	9.90	10.50
L2	2.50	2.80	3.10
H	0.40	0.70	1.05
M	4.90	5.30	5.60
N	2.09	2.29	2.49

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